

10CTQ150 10CTQ150S

Technical Data Data Sheet N1308, Rev. B

RoHS 🗭

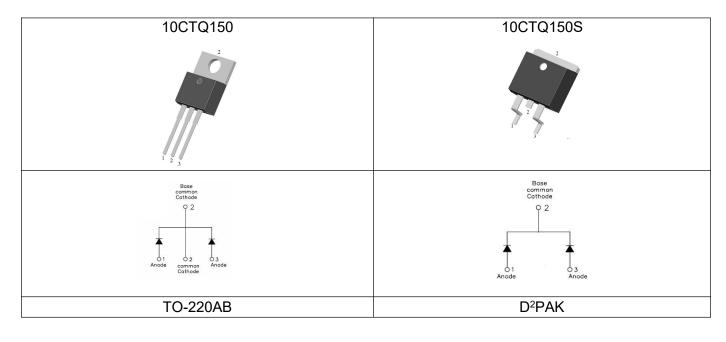
10CTQ150 10CTQ150S SCHOTTKY RECTIFIER

Features

- 175 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection



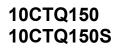
Maximum Ratings@Tc=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	150	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=155°C, rectangular wave form	5(Per Leg) 10(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	138	A

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (per leg)*	V _{F1}	@ 5A, Pulse, TJ = 25 °C @ 10A, Pulse, TJ = 25 °C	0.84 0.93	0.93 1.10	V
	V _{F2}	@ 5A, Pulse, TJ = 125 °C @ 10A, Pulse, TJ = 125 °C	0.71 0.81	0.73 0.86	V
Reverse Current (per leg)*	I _{R1}	@V _R = rated V _R T _J = 25 ℃	0.001	0.05	mA
	I _{R2}	@V _R = rated V _R T _J = 125 ℃	0.1	7.0	mA
Junction Capacitance (per leg)	CT	@V _R = 5V, T _C = 25 ℃ f _{SIG} = 1MHz	91	200	pF
Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Max. Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

 $^{\star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

Thermal-Mechanical Specifications:

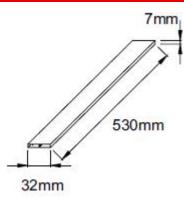
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case(per leg)	R _{θJC}	DC operation	3.5	°C/W
Maximum Thermal Resistance Junction to Case(per package)	R _{0JC}	DC operation	1.75	°C/W
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.50	°C/W
Case Style	TO-220AB D ² PAK			

Tube Specification

Device	Package	Weight	Shipping
10CTQ150	TO-220AB	1.8g	50pcs / tube
10CTQ150S	D ² PAK	1.85g	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification(TO-220AB)

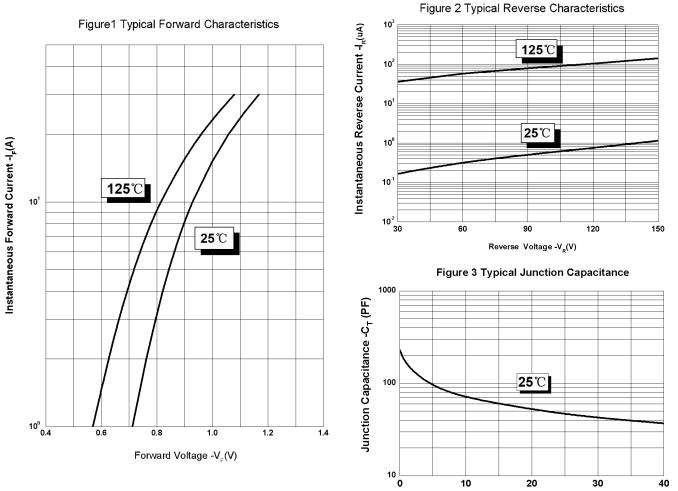


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Ratings and Characteristics Curves



Reverse Voltage -V_R(V)



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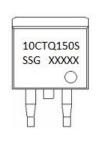
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Marking Diagram



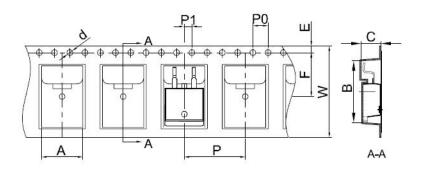


Where XXXXX is YYWWL

10	= Forward Current (10A)
С	= Configuration
TQ	= Device Type
150	= Reverse Voltage (150V)
S	= Package type
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK



Symbol	Millimeters		
	Min.	Max.	
А	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	



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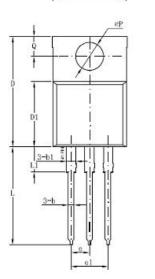


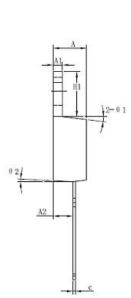
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Mechanical Dimensions TO-220AB

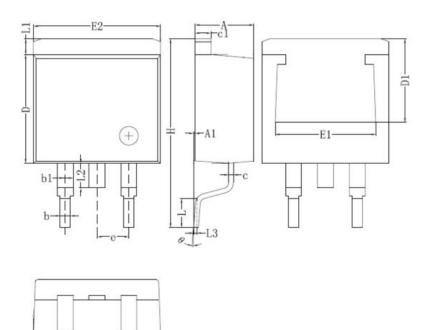






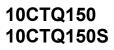
Symbol	Dimensions in millimeters		
	Min	Typical	Max
А	3.56	-	4.83
A1	0.51	-	1.4
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
С	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	9.65	-	10.67
е	-	2.54	-
e1	-	5.08	-
H1	5.84	-	6.86
L	12.7	-	14.73
L1	-	-	6.35
ΦP	-	3.56	-
Q	2.54	-	3.43

Mechanical Dimensions D²PAK



Cumb al	Dimensions in millimeters		
Symbol	Min.	Max.	
А	4.06	4.83	
A1	0	0.26	
b	0.51	0.99	
b1	1.14	1.78	
С	0.31	0.74	
c1	1.14	1.65	
D	8.38	9.65	
D1	6.4		
E1	6.22		
E2	9.65	10.67	
е	2.54BSC		
Н	14.6	15.88	
L	1.78	2.8	
L1	-	1.68	
L2	-	2.2	
L3	0.255BSC		
Θ	0	8°	







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